

SILICON TRANSISTORS

2SA1221, 1222

PNP SILICON EPITAXIAL TRANSISTOR FOR LOW-FREQUENCY POWER AMPLIFIERS

FEATURES

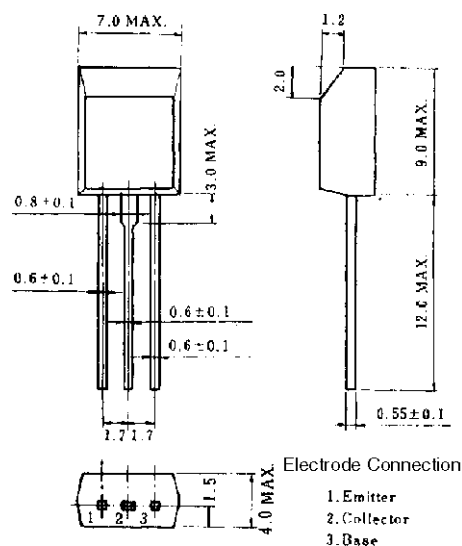
- Ideal for use of high withstanding voltage current such as TV vertical deflection output, audio output, and variable power supplies.
- Complementary transistor with 2SC2958 and 2SC2959
 $V_{CEO} = 140\text{ V}$: 2SA1221/2SC2958
 $V_{CEO} = 160\text{ V}$: 2SA1222/2SC2959

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-160	V
Collector to emitter voltage	V_{CEO}	-140/-160	V
Emitter to base voltage	V_{EBO}	-5.0	V
Collector current (DC)	$I_{C(DC)}$	-500	mA
Collector current (pulse)	$I_{C(pulse)^*}$	-1.0	A
Total power dissipation	P_T	1.0	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10\text{ ms}$, duty cycle $\leq 50\%$

PACKAGE DRAWING (UNIT: mm)



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -100\text{ V}$, $I_E = 0$			-200	nA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5.0\text{ V}$, $I_C = 0$			-200	nA
DC current gain	h_{FE}^{**}	$V_{CE} = -2.0\text{ V}$, $I_C = -100\text{ mA}$	100	150	400	
DC base voltage	V_{BE}^{**}	$V_{CE} = -5.0\text{ V}$, $I_C = -20\text{ mA}$	-0.6	-0.64	-0.7	V
Collector saturation voltage	$V_{CE(sat)}^{**}$	$I_C = -1.0\text{ A}$, $I_B = -0.2\text{ A}$		-0.6	-0.9	V
Base saturation voltage	$V_{BE(sat)}^{**}$	$I_C = -1.0\text{ A}$, $I_B = -0.2\text{ A}$		-1.1	-0.3	V
Output capacitance	C_{ob}	$V_{CB} = -10\text{ V}$, $I_E = 0$, $f = 1.0\text{ MHz}$		24	40	pF
Gain bandwidth product	f_r	$V_{CE} = -10\text{ V}$, $I_E = 20\text{ mA}$	30	45		MHz

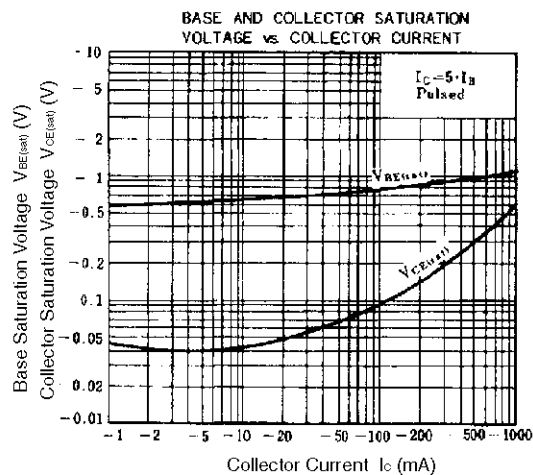
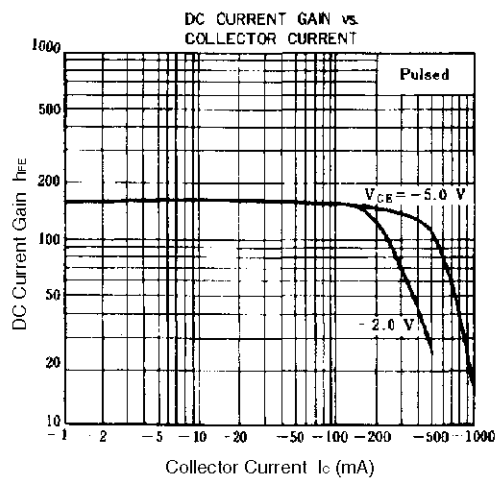
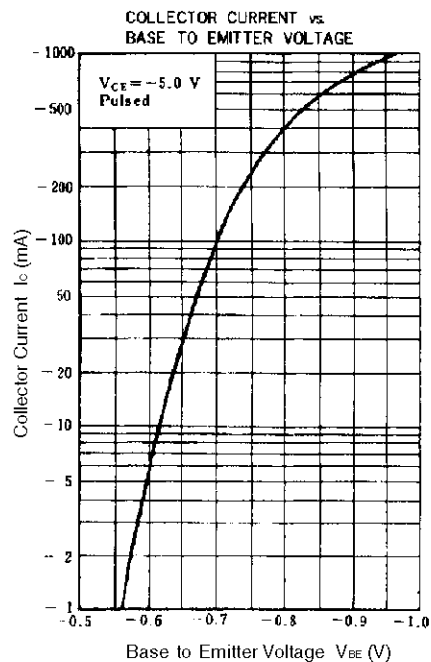
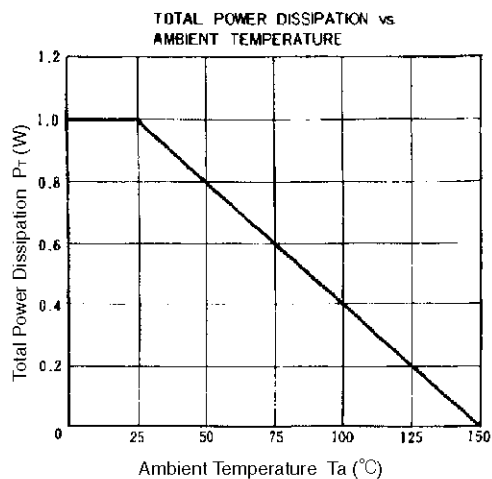
** Pulse test $PW \leq 350\text{ }\mu\text{s}$, duty cycle $\leq 2\%$ per pulsed

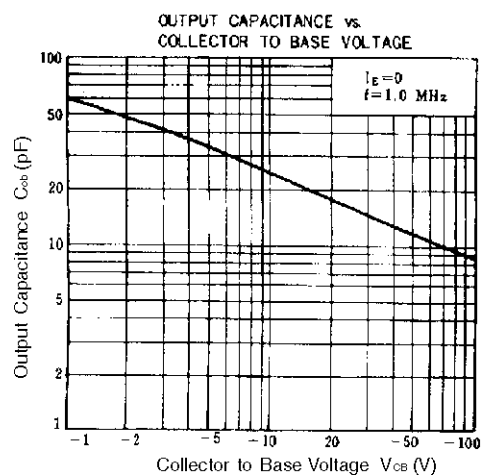
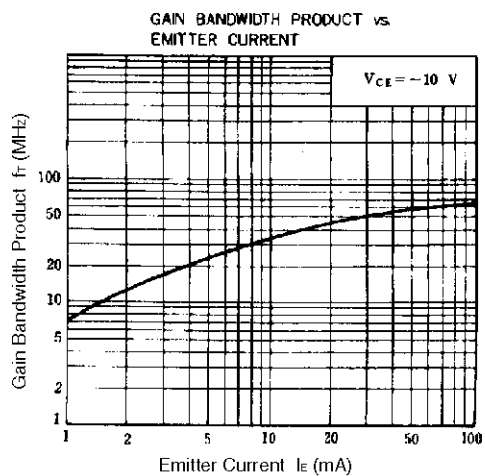
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hFE CLASSIFICATION

Marking	M	L	K
hFE	100 to 200	160 to 320	200 to 400

TYPICAL CHARACTERISTICS (Ta = 25°C)





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